NSN 5962-01-111-1245

Memory Microcircuit - Page 1 of 2



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Unit Of Meas	ure:
N/a	
Shelf Life:	
16 printed circ	
	-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Test Data Do	
Rom	
Memory Devi	се туре:
output	
	conds propagation delay time, low to high level output and 25.00 nanoseconds propagation delay time, high to low l
	Per Chacteristic:
7.0 volts pow	
	ng And Type Per Characteristic:
Solder	
	face Treatment:
D-2 mil-m-385	
	Source And Designator:
10 input	
Input Circuit	Pattern:
Transistor-trar	
Output Logic	Form:
Dual-in-line	
Inclosure Co	nfiguration:
Ceramic	
Inclosure Ma	terial:
Hermetically s	sealed and monolithic and programmable and 3-state output
Features Pro	vided:
-65.0/+150.0 (degrees celsius
Storage Tem	purature Range:
+0.0/+75.0 de	grees celsius
Operating Te	empurature Range:
500.0 milliwat	ts
Maximum Po	ower Dissipation Rating:
0.185 inches	
Body Height:	
	0 inches and 0.310 inches
Body Width:	
0.840 inches	

Yes - demil/mli

NSN 5962-01-111-1245

Memory Microcircuit - Page 2 of 2

Fiig: A458a0

